What is claimed is:

- 1. A method for forming a micro pattern, comprising the steps of:
- (a) providing a semiconductor substrate in which a lower film is formed;
- (b) coating a first photoresist film on the lower film;
- (c) depositing a second photoresist film having a higher glass transition temperature than the first photoresist film on the first photoresist film;
- (d) implementing an exposure process and a wet development process using a photo mask to pattern the second photoresist film and the first photoresist film, thereby forming a first photoresist film pattern;
- (e) implementing RFP for the first photoresist film pattern to cause flow of the first photoresist film pattern, thus forming a second photoresist film pattern having a lower critical dimension than the first photoresist film pattern; and
- (f) implementing an etch process using the second photoresist film
 pattern as an etch mask for the lower film to pattern the lower film.
 - 2. The method as claimed in claim 1, wherein the lower film is formed using TiN, SiON, Si₃N₄, organic anti-reflection coating of amorphous carbon series or an inorganic anti-reflection coating.

20

5

10

3. The method as claimed in claim 1, wherein the difference in a glass transition temperature between the first photoresist film and the second photoresist film is $1 \sim 10 \, ^{\circ}\text{C}$.

- 4. The method as claimed in claim 1, wherein the first photoresist film and the second photoresist film have the same physical properties other than the glass transition temperature.
- 5. The method as claimed in claim 1, wherein the first photoresist film is coated in thickness of 0.1 μ m.

5

10

6. The method as claimed in claim 1, wherein the second photoresist film is coated in thickness of 0.5 μ m.

7. The method as claimed in claim 1, wherein the exposure process employs I-line, KrF, ArF, EUV, E-beam or X-ray as a photoresist.

- 8. The method as claimed in claim 1, wherein during the RFP, a heating time is $50 \sim 200$ seconds.
 - 9. The method as claimed in claim 1, wherein the RFP is implemented at a temperature of 132 °C for 90 seconds.
- 20 10. The method as claimed in claim 1, wherein the critical dimension of the first photoresist film pattern is 0.20 μ m.
 - 11. The method as claimed in claim 1, wherein the critical dimension of the second photoresist film pattern is 0.13 μ m.